



40V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C (Note 5)	
40V	3.7 m Ω @ V _{GS} = 10V	100A	

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Q_g Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH4005SPSWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

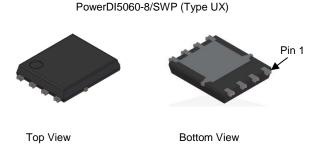
Description and Applications

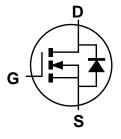
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine management systems
- Body control electronics
- DC-DC converters

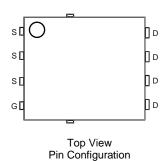
Mechanical Data

- Package: PowerDI[®]5060-8
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)





Internal Schematic



Ordering Information (Note 4)

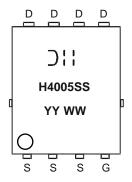
Part Number	Packago	Packing		
Fait Nullibei	Package	Qty.	Carrier	
DMTH4005SPSWQ-13	PowerDI5060-8/SWP (Type UX)	2,500	Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.
- 5. Package limited.



Marking Information



);; = Manufacturer's Marking H4005SS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 23 = 2023) WW = Week (01 to 53)

Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	40	V
Gate-Source Voltage		Vgss	±20	V
Continuous Drain Current (Note 6)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	lo	20.9 17.5	А
Continuous Drain Current (Notes 5 & 7) $ T_C = +25^{\circ}C $ $T_C = +100^{\circ}C $		lo	100 100	А
Maximum Continuous Body Diode Forward Current (Note 7)	Is	100	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		IDM	150	А
Avalanche Current, L = 0.6mH		las	21	А
Avalanche Energy, L = 0.6mH		Eas	132.3	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T _A = +25°C	PD	2.6	W
Thermal Resistance, Junction to Ambient (Note 6)		Reja	57	°C/W
Total Power Dissipation (Note 7) $T_C = +25^{\circ}C$		P _D	150	W
Thermal Resistance, Junction to Case (Note 7)		ReJC	1	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Notes:

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.7. Thermal resistance from junction to soldering point (on the exposed drain pad).



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

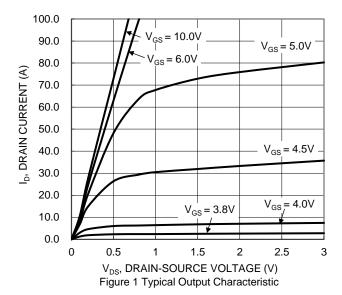
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BVDSS	40	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_		1	μΑ	V _{DS} = 32V, V _{GS} = 0V	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	Vgs(TH)	2		4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		2.9	3.7	mΩ	$V_{GS} = 10V, I_D = 50A$	
Diode Forward Voltage	V_{SD}	_	0.88		V	$V_{GS} = 0V, I_S = 50A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss		3,062	_	pF	V _{DS} = 20V, V _{GS} = 0V f = 1MHz	
Output Capacitance	C_{oss}	_	902.2				
Reverse Transfer Capacitance	Crss	_	179.2	_			
Gate Resistance	Rg		0.67	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg		49.1			V _{DD} = 20V, I _D = 50A V _{GS} = 10V	
Gate-Source Charge	Qgs	_	10.3		nC		
Gate-Drain Charge	Qgd	_	13				
Turn-On Delay Time	td(ON)	_	8.7			$V_{DD} = 20V, V_{GS} = 10V$ $I_{D} = 50A, R_{g} = 3\Omega$	
Turn-On Rise Time	t _R		6.8	_	ns		
Turn-Off Delay Time	tD(OFF)	_	18.6	_	115		
Turn-Off Fall Time	tF	_	7.3	_			
Body Diode Reverse Recovery Time	trr	_	31.8		ns	I F0A dl/dt _ 100A/uc	
Body Diode Reverse Recovery Charge	Q _{RR}	_	26.5	_	nC	I _F = 50A, dI/dt = 100A/μs	

Notes:

^{8.} Short duration pulse test used to minimize self-heating effect. 9. Guaranteed by design. Not subject to product testing.







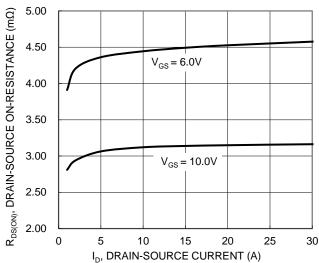


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

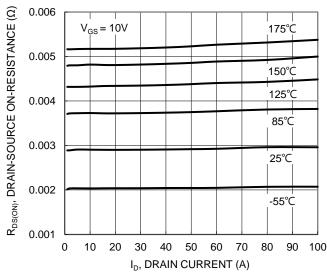
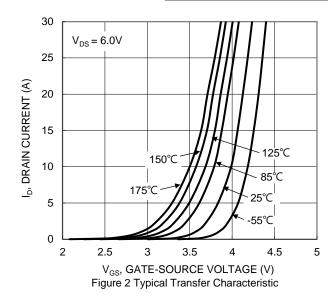
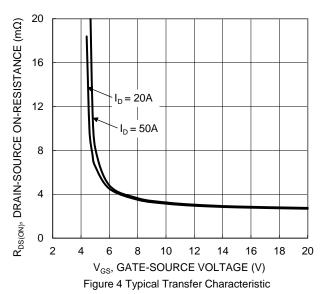


Figure 5 Typical On-Resistance vs. Drain Current and Temperature





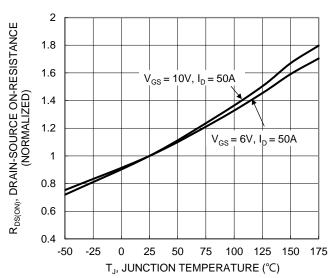


Figure 6 On-Resistance Variation with Temperature





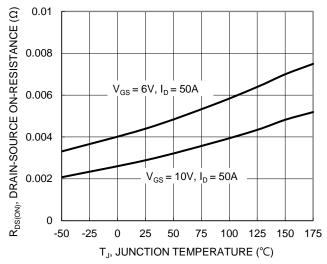


Figure 7 On-Resistance Variation with Temperature

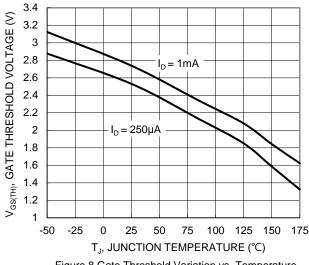
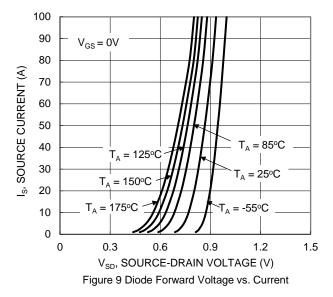
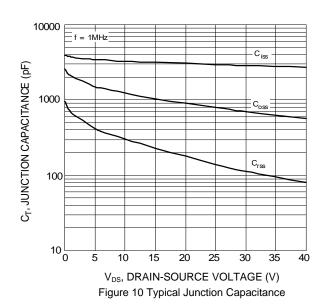
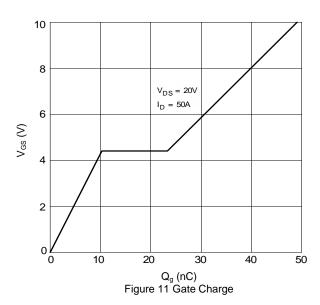
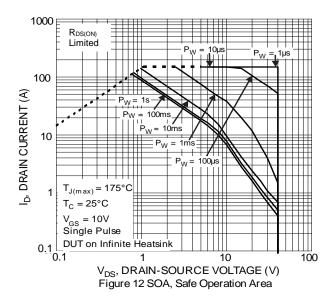


Figure 8 Gate Threshold Variation vs. Temperature











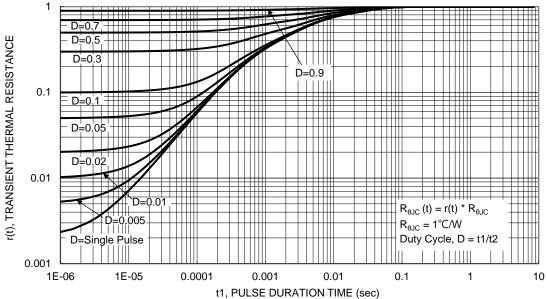


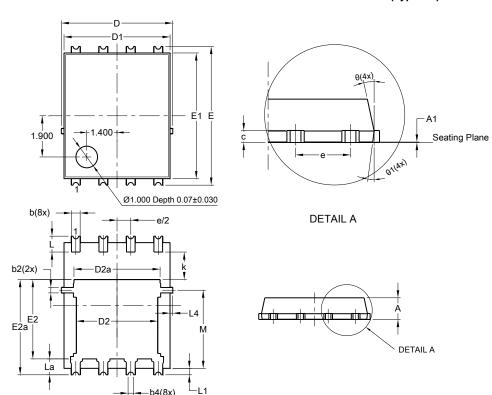
Figure 13 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UX)

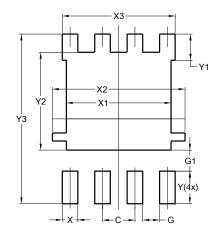


PowerDI5060-8/SWP (Type UX)					
Dim	Min Max		Тур		
Α	0.90	1.10	1.00		
A1	0	0.05			
b	0.30	0.50	0.41		
b2	0.20	0.35	0.25		
b4	().25REF	=		
С	0.230	0.330	0.277		
D	5	.15 BS0	2		
D1	4.70	5.10	4.90		
D2	3.56	3.76			
D2a	3.78	3.98			
Е	6	.40 BS0	0		
E1	5.60	6.00	5.80		
E2	3.46	3.86	3.66		
E2a	4.195	4.595	4.395		
е	1	.27BS0)		
k	1.05				
L	0.635	0.835	0.735		
La	0.635	0.835	0.735		
L1	0.200	0.400	0.300		
L1a	0.050REF				
L4	0.025	0.225	0.125		
М	3.205	4.005	3.605		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UX)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	4.100		
X2	5.190		
Х3	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



IMPORTANT NOTICE

- 1. DIODES INCORPORATED (Diodes) AND ITS SUBSIDIARIES MAKE NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO ANY INFORMATION CONTAINED IN THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).
- 2. The Information contained herein is for informational purpose only and is provided only to illustrate the operation of Diodes' products described herein and application examples. Diodes does not assume any liability arising out of the application or use of this document or any product described herein. This document is intended for skilled and technically trained engineering customers and users who design with Diodes' products. Diodes' products may be used to facilitate safety-related applications; however, in all instances customers and users are responsible for (a) selecting the appropriate Diodes products for their applications, (b) evaluating the suitability of Diodes' products for their intended applications, (c) ensuring their applications, which incorporate Diodes' products, comply the applicable legal and regulatory requirements as well as safety and functional-safety related standards, and (d) ensuring they design with appropriate safeguards (including testing, validation, quality control techniques, redundancy, malfunction prevention, and appropriate treatment for aging degradation) to minimize the risks associated with their applications.
- 3. Diodes assumes no liability for any application-related information, support, assistance or feedback that may be provided by Diodes from time to time. Any customer or user of this document or products described herein will assume all risks and liabilities associated with such use, and will hold Diodes and all companies whose products are represented herein or on Diodes' websites, harmless against all damages and liabilities.
- 4. Products described herein may be covered by one or more United States, international or foreign patents and pending patent applications. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks and trademark applications. Diodes does not convey any license under any of its intellectual property rights or the rights of any third parties (including third parties whose products and services may be described in this document or on Diodes' website) under this document.
- 5. Diodes' products are provided subject to Diodes' Standard Terms and Conditions of Sale (https://www.diodes.com/about/company/terms-and-conditions/terms-and-conditions-of-sales/) or other applicable terms. This document does not alter or expand the applicable warranties provided by Diodes. Diodes does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.
- 6. Diodes' products and technology may not be used for or incorporated into any products or systems whose manufacture, use or sale is prohibited under any applicable laws and regulations. Should customers or users use Diodes' products in contravention of any applicable laws or regulations, or for any unintended or unauthorized application, customers and users will (a) be solely responsible for any damages, losses or penalties arising in connection therewith or as a result thereof, and (b) indemnify and hold Diodes and its representatives and agents harmless against any and all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim relating to any noncompliance with the applicable laws and regulations, as well as any unintended or unauthorized application.
- 7. While efforts have been made to ensure the information contained in this document is accurate, complete and current, it may contain technical inaccuracies, omissions and typographical errors. Diodes does not warrant that information contained in this document is error-free and Diodes is under no obligation to update or otherwise correct this information. Notwithstanding the foregoing, Diodes reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes.
- 8. Any unauthorized copying, modification, distribution, transmission, display or other use of this document (or any portion hereof) is prohibited. Diodes assumes no responsibility for any losses incurred by the customers or users or any third parties arising from any such unauthorized use.
- 9. This Notice may be periodically updated with the most recent version available at https://www.diodes.com/about/company/terms-and-conditions/important-notice

The Diodes logo is a registered trademark of Diodes Incorporated in the United States and other countries. All other trademarks are the property of their respective owners.

© 2023 Diodes Incorporated. All Rights Reserved.

www.diodes.com